## Confirmation No. 6408

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Meunier-Beillard et al.

Examiner:

Khiem Nguyen

Serial No.:

10/550,853

Group Art Unit:

2823

Filed:

September 22, 2005

Docket No.:

NL030357 US1

Title:

METHOD OF EPITAXIAL DEPOSITION OF AN N-DOPED SILICON

LAYER

## **OFFICE ACTION RESPONSE**

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Customer No. 65913

## Dear Sir:

In response to the non-final Office Action dated April 30, 2008, please reconsider the application in view of the following amendments and remarks.

A complete listing of the claims, to include any amendments presented therein, begins on page 2 of this paper.

Remarks/Arguments follow on page 6.

Authorization is provided to charge/credit Deposit Account 50-0996 (NXPS.265PA) any requisite fees/overages to enter this paper.